

Cont  
B1

3 a via-hole through the semiconductor substrate, the via-hole having a metal film on  
4 an inside wall;  
5 a wiring metal layer formed in a spiral pattern with an inside end on the  
6 semiconductor substrate, the wiring metal layer being electrically connected to the via-hole at the  
7 inside end;  
8 an inductor of metal film formed in a spiral pattern with an inside end on the wiring  
9 metal layer with the inside end of the inductor film being near the via-hole; and  
10 a dielectric layer between the spiral wiring metal layer and the spiral inductor metal  
11 film.

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B2

1 9. (Amended) An RF choke used in at least one of a matching circuit and a bias  
2 feeding circuit, both circuits being included in an RF amplifier, the RF choke comprising:  
3 a semiconductor substrate where at least one of the matching circuit and the bias  
4 feeding circuit is incorporated;  
5 a via-hole through the semiconductor substrate, the via-hole having a metal film on  
6 an inside wall;  
7 a wiring metal layer formed in a spiral pattern with an inside end on the  
8 semiconductor substrate, the wiring metal layer being electrically connected to the via-hole at the  
9 inside end;  
10 an inductor of metal film formed in a spiral pattern with an inside end on the wiring  
11 metal layer with the inside end of the inductor film being near the via-hole; and  
12 a dielectric layer between the spiral wiring metal layer and the spiral inductor metal  
13 film.

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